



DMT34M2LPS

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
30V	3.2mΩ @ V _{GS} = 10V	100A
	5.2mΩ @ V _{GS} = 4.5V	80A

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

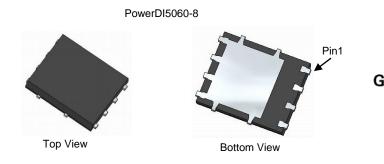
Features and Benefits

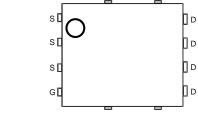
- Low R_{DS(ON)} Minimizes On-State Losses
- Excellent Q_{gd} x R_{DS(ON)} Product (FOM)
- Advanced Technology for DC-DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- 100% Unclamped Inductive Switching Ensures More Reliability
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.097 grams (Approximate)

D





S Internal Schematic

Top View Pin Configuration

Ordering Information (Note 4)

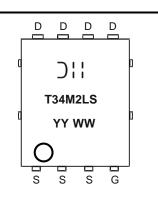
	Part Number	Case	Packaging			
DMT34M2LPS-13		PowerDI5060-8	2,500/Tape & Reel			
Notes:	Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.					

EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	30	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, V_{GS} = 10V (Note 6)	T _A = +25°C T _A = +70°C	ID	21 17	А
Continuous Drain Current, V_{GS} = 10V (Note 7)	T _C = +25°C T _C = +70°C	ID	100 80	А
Maximum Continuous Body Diode Forward Current (Not	te 6)	Is	3	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	250	А	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I _{SM}	250	А
Avalanche Current, L=0.1mH (Note 8)		IAS	38.5	А
Avalanche Energy, L=0.1mH (Note 8)		E _{AS}	78	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	98	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	58	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	PD	42	W
Thermal Resistance, Junction to Case (Note 7)		R ₀ JC	2.5	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}		_	±100	nA	$V_{GS} = 20V, V_{DS} = 0V$ $V_{GS} = -16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1.0	_	3.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	2.6	3.2	mΩ	$V_{GS} = 10V, I_D = 20A$	
	R _{DS(ON)}	_	3.7	5.2	11122	$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_S = 2A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}		2242	-	pF	V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	960	—			
Reverse Transfer Capacitance	C _{rss}	_	217	—			
Gate Resistance	R _g	_	1.0	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	_	39	—		V _{DD} = 15V, I _D = 20A	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	20	—	nC		
Gate-Source Charge	Q _{gs}	_	5.6	—	nc		
Gate-Drain Charge	Q _{gd}	_	7.0	—			
Turn-On Delay Time	t _{D(ON)}	_	5.6	_		$V_{DD} = 15V, V_{GS} = 10V,$ $R_g = 3\Omega, I_D = 20A$	
Turn-On Rise Time	t _R	_	13.8	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	22.4	—			
Turn-Off Fall Time	tF	_	11.4	—	1		
Reverse Recovery Time	t _{RR}		22	_	ns	I _F = 15A, dl/dt = 500A/µs	
Reverse Recovery Charge	Q _{RR}	_	27	_	nC	I _F = 15A, dl/dt = 500A/µs	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

7. Thermal resistance from junction to soldering point (on the exposed drain pad).

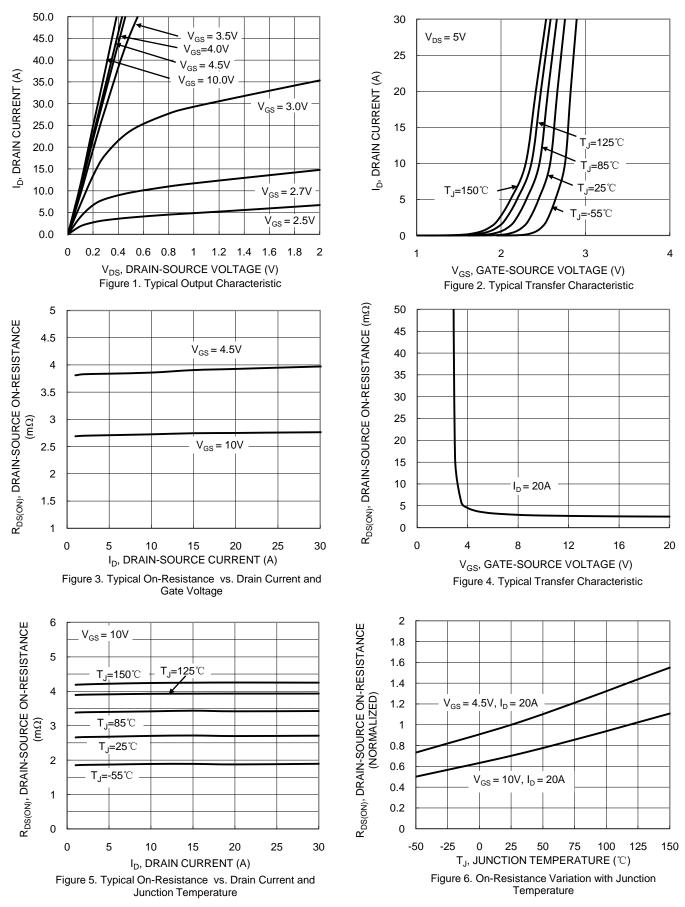
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

9. Short duration pulse test used to minimize self-heating effect.

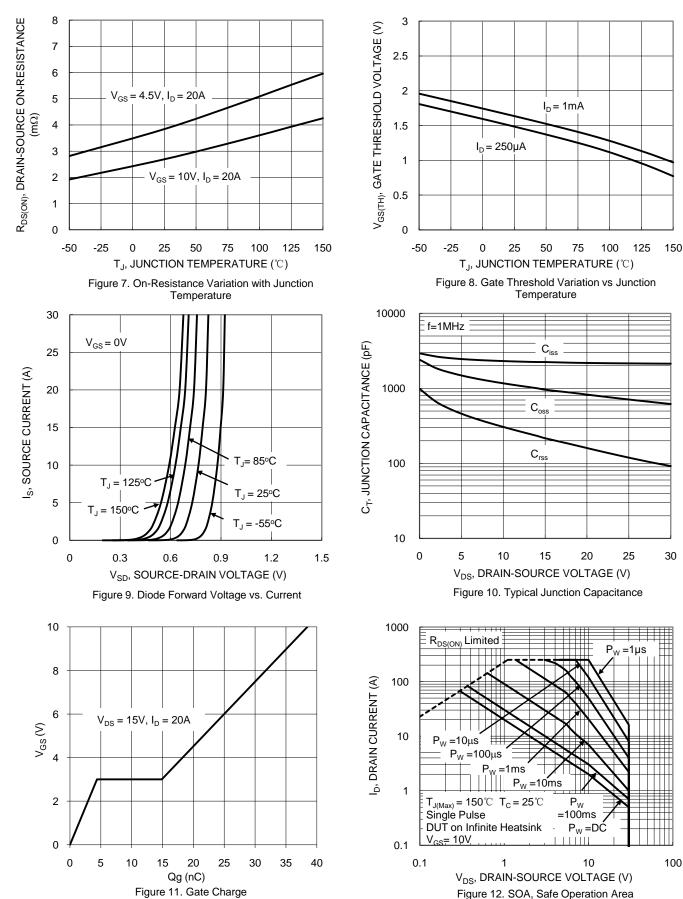
10. Guaranteed by design. Not subject to product testing.



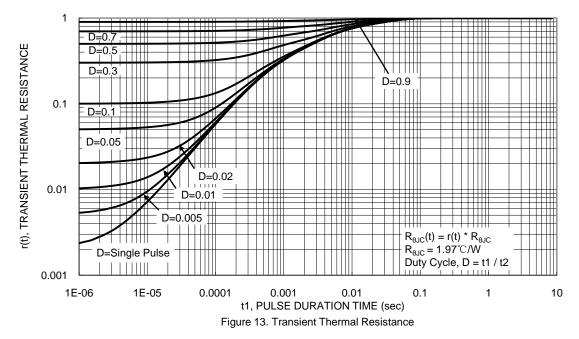
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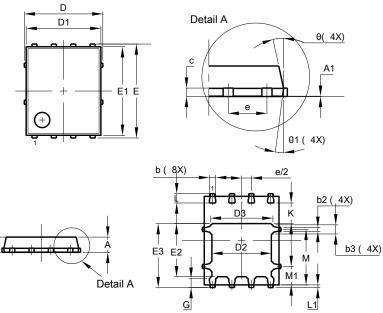




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

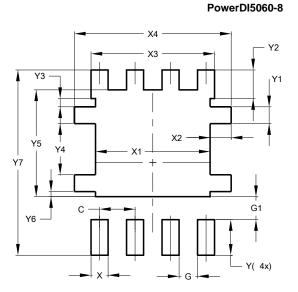
PowerDI5060-8



PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D		5.15 BSC			
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90 4.30		4.10		
E		6.15 BSC	;		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е		1.27 BSC	;		
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions Value (in mm) С 1.270 0.660 G G1 0.820 Х 0.610 X1 4.100 X2 0.755 Х3 4.420 X4 5.610 Υ 1.270 Y1 0.600 Y2 1.020 Y3 0.295 Y4 1.825 Y5 3.810 Y6 0.180 Y7 6.610



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